KTB1368

Rev.F Mar.-2016

DATA SHEET

/ Descriptions

WR0553I ṂṂ Ł SQS ÆṀ ɥ s ǁ ˥ Silicon PNP transistor in a TO-220F Plastic Package.

/ Features

kIH ɬ ớ Ḅ/љ NWG5393 Ӣ ´

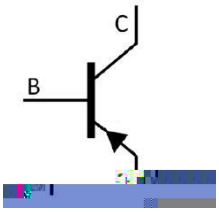
Good Linearity of h_{FE}, complementary pair with KTD2060.

/ Applications

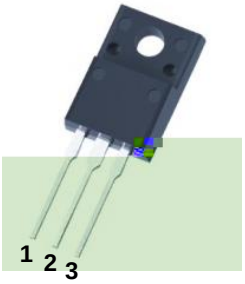
ȓ̂ ̂ ̂ ̆ ǫ̈ ƶ

General Purpose Application.

/ Equivalent Circuit



/ Pinning



PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

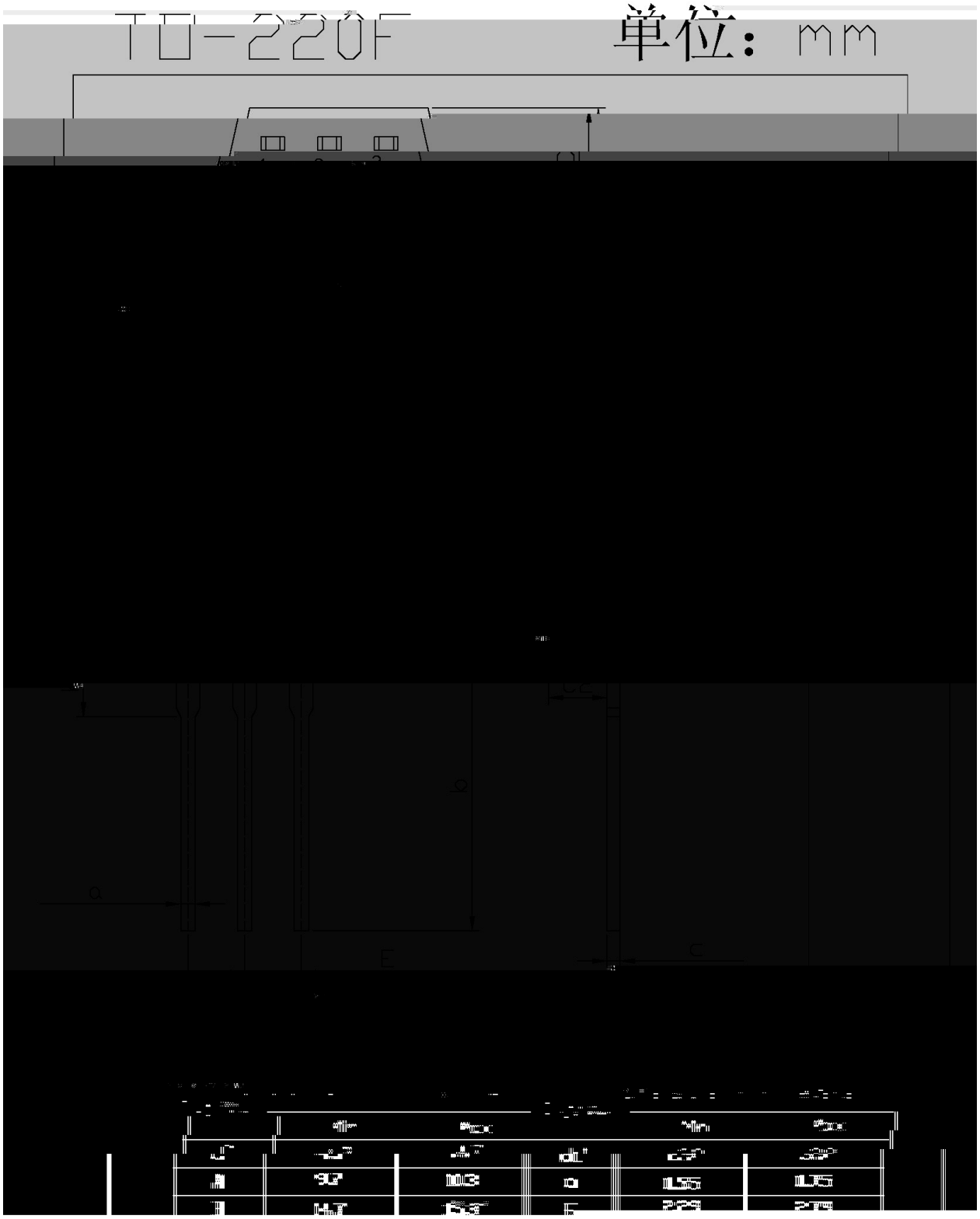
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	R	O	Y
h_{FE} Range	40~80	70~140	120~240

v ̈Ω Parameter	˧ N Symbol	̈Ω Ö Rating	D Ĥ Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5	V
Collector Current - Continuous	I_C	-4	A
Base Current	I_B	-0.4	A
Collector Power Dissipation	P_C(Tc=25)	25	W
Junction Temperature	T_j	150	ł
Storage Temperature Range	T_{stg}	-55 Ḱ 150	ł

v ̈Ω Parameter	˧ N Symbol	˩ ⁝ ˥ Ţ Test Conditions	ω ṇ Ö Min	Ɛ ʒ Ö Typ	ω ᶻ Ö Max	ƶ19CÀH88hEIFSC Ɛ ɟ

/ Package Dimensions



( ) / Temperature Profile for Dip Soldering(Pb-Free)



ب ˝ χ

1 ʃ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ö □ ỷ 255 ° 5 ɬ ı `H ڑ ˈY ⺈ ⺮ 5 ° 0.5sec;

3 ì ˙ ˥ ˛ ɔ ھ ỷ ⺮ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.